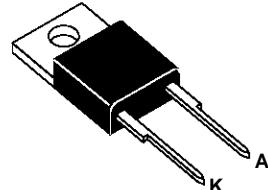


HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- INSULATED PACKAGE :
Insulating voltage = 2500 V_{RMS}
Capacitance = 7 pF



isolated
TO220AC
(Plastic)

BYW80PI-200

DESCRIPTION

Single chip rectifier suited for switchmode power supply and high frequency DC to DC converters. Packaged in Isolated TO220AC, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
I _{F(RMS)}	RMS forward current		20	A
I _{F(AV)}	Average forward current $\delta = 0.5$	T _c =110°C	10	A
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	100	A
T _{stg} T _j	Storage and junction temperature range		- 65 to + 150 - 65 to + 150	°C °C

Symbol	Parameter	BYW80PI-				Unit
		50	100	150	200	
V _{RRM}	Repetitive peak reverse voltage	50	100	150	200	V

BYW80PI

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-c)	Junction to case	3.5	°C/W

ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I _R *	T _j = 25°C	V _R = V _{RRM}			10	μA
	T _j = 100°C				1	mA
V _F **	T _j = 125°C	I _F = 7 A			0.85	V
	T _j = 125°C	I _F = 15 A			1.05	
	T _j = 25°C	I _F = 15 A			1.15	

Pulse test : * tp = 5 ms, duty cycle < 2 %

** tp = 380 μs, duty cycle < 2 %

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.027 \times I_F^2(\text{RMS})$$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	T _j = 25°C	I _F = 0.5A	I _{rr} = 0.25A		25	ns
		I _F = 1A	V _R = 30V		35	
tfr	T _j = 25°C	I _F = 1A	V _{FR} = 1.1 x V _F	tr = 10 ns	15	ns
V _{FP}	T _j = 25°C	I _F = 1A		tr = 10 ns	2	V

Fig.1 : Average forward power dissipation versus average forward current.

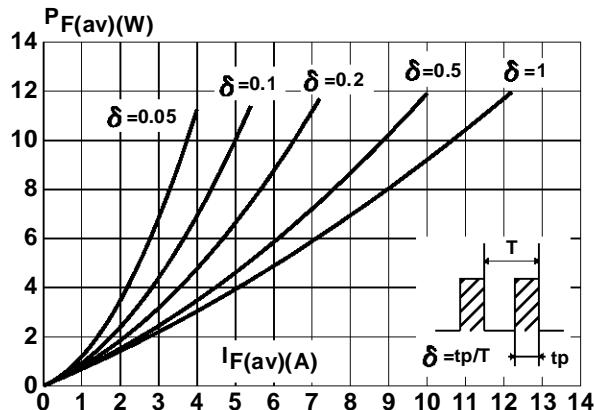


Fig.3 : Forward voltage drop versus forward current (maximum values).

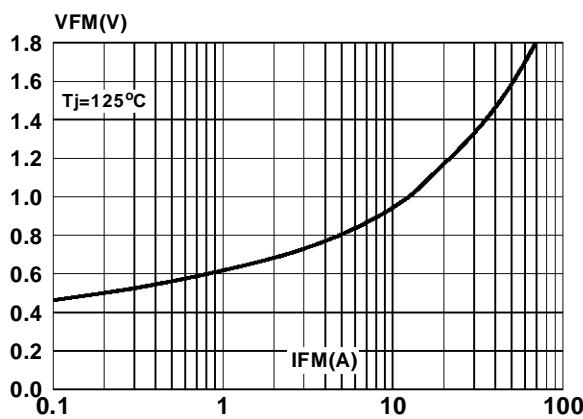


Fig.5 : Non repetitive surge peak forward current versus overload duration.

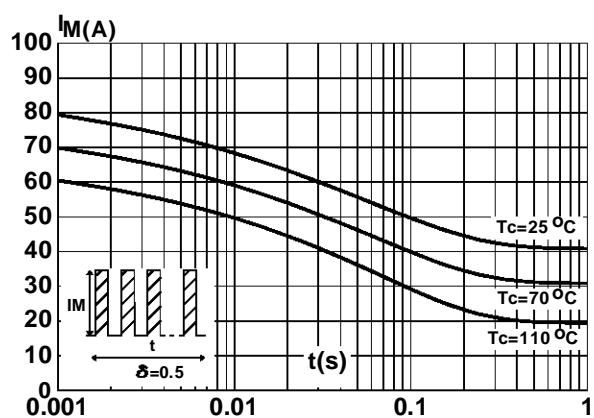


Fig.2 : Peak current versus form factor.

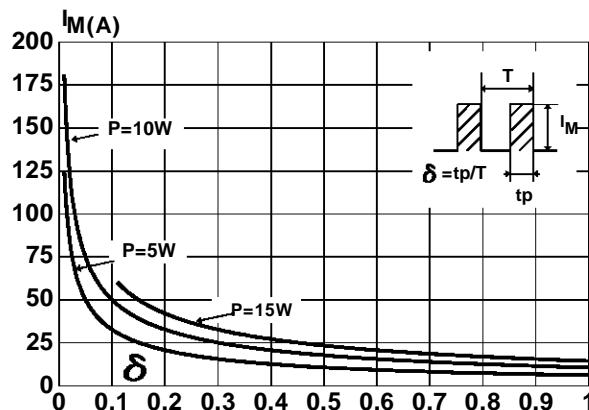


Fig.4 : Relative variation of thermal impedance junction to case versus pulse duration.

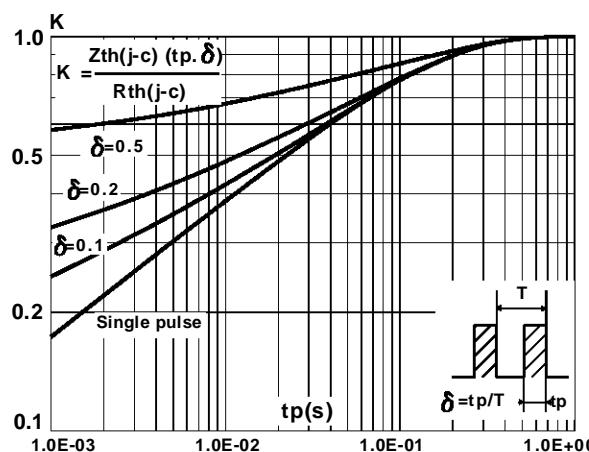
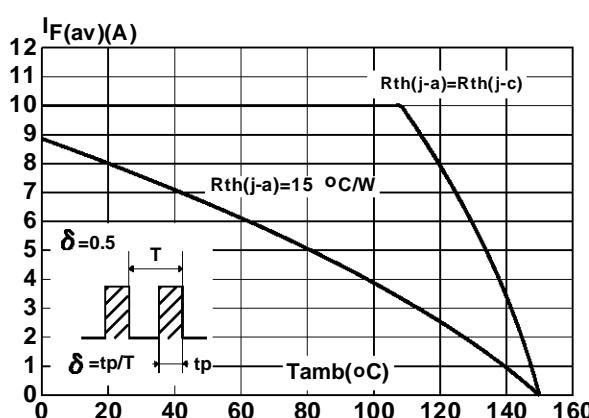


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



BYW80PI

Fig.7 : Junction capacitance versus reverse voltage applied (Typical values).

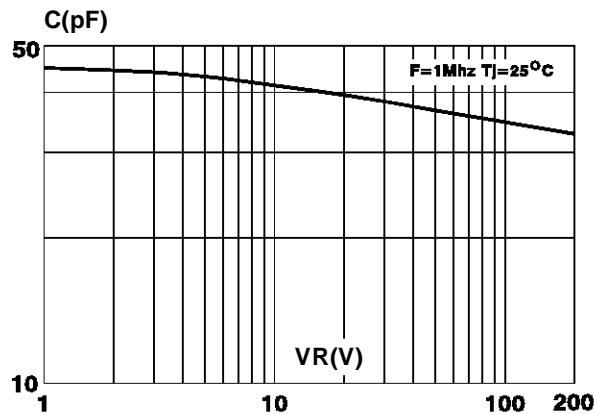


Fig.9 : Peak reverse current versus dIF/dt.

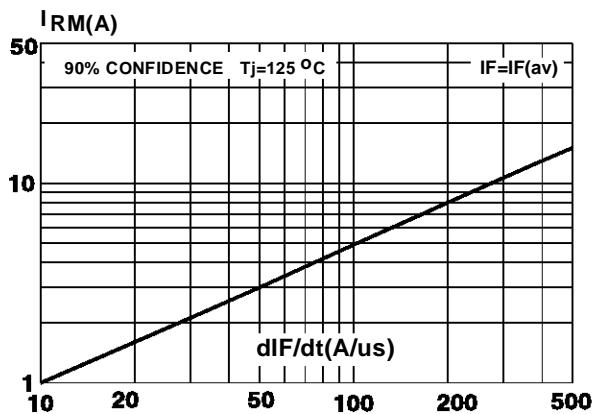


Fig.8 : Recovery charges versus dIF/dt.

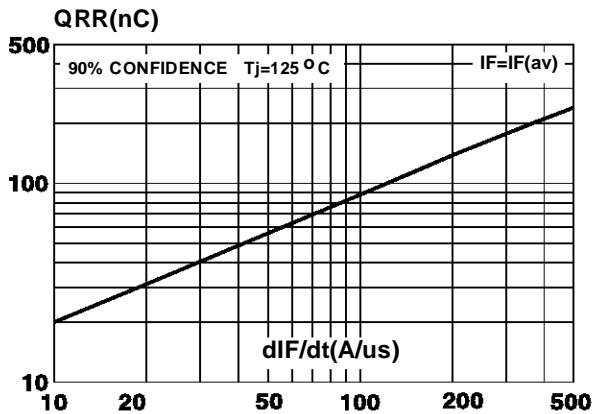
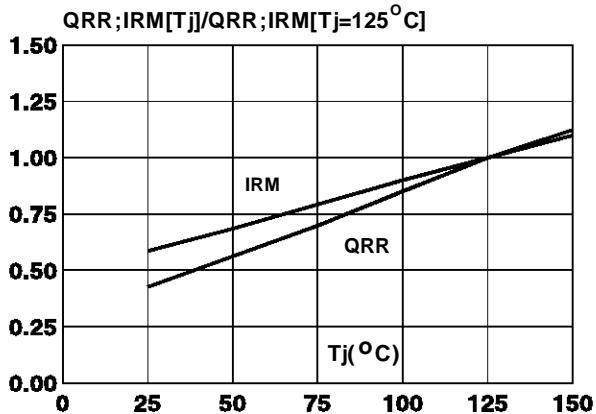
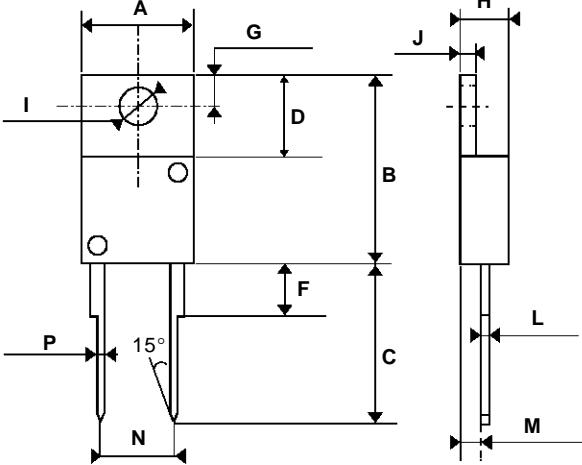


Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA

TO220AC (isolated)



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10.20	10.40	0.401	0.401
B	14.23	15.87	0.560	0.625
C	12.70	14.70	0.500	0.579
D	5.85	6.85	0.230	0.270
F		4.50		0.178
G	2.54	3.00	0.100	0.119
H	4.48	4.82	0.176	0.190
I	3.55	4.00	0.139	0.158
J	1.15	1.39	0.045	0.055
L	0.35	0.65	0.013	0.026
M	2.10	2.70	0.082	0.107
N	4.58	5.58	0.18	0.22
P	0.64	0.96	0.025	0.038

Cooling method : C

Marking : Type number

Weight : 2.2 g

Recommended torque value : 0.8m.N

Maximum torque value : 1.0m.N

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